



SINGLE N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	57mΩ @ V _{GS} = 10V	6.0A
30V	112mΩ @ V _{GS} = 4.5V	3.8A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074g (Approximate)



Ordering Information (Note 4)

Part Number		Case	Packaging
DMN3112SSS-13		SOP-8L	2,500/Tape & Reel
	10000		

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





] || = Manufacturer's Marking
 N3112SS = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 13 = 2013)
 WW = Week (01 - 53)
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +70°C	ID	6 4.5	A
Pulsed Drain Current (Note 6)			I _{DM}	24	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	50	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Sympol	Mim	Tim	Max	Ilmit	Test Condition
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	<u> </u>	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}			800	nA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}			±80	nA	V_{GS} = ±20V, V_{DS} = 0V
eate eearee Eearage	-GSS	+		±800		$V_{GS} = \pm 25 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}		—	2.2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	RDS(ON)		43	57	mΩ	V _{GS} = 10V, I _D = 5.8A
	TUS(UN)		83	112	11152	V _{GS} = 4.5V, I _D = 3.7A
Forward Transconductance	9fs		2.8		S	V _{DS} = 10V, I _D = 3.7A
Diode Forward Voltage (Note 7)	V _{SD}	0.5	0.8	1.2	V	V _{GS} = 0V, I _S = 2.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}		268	_	pF	
Output Capacitance	C _{oss}		73		pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		50		pF	

5. Device mounted on 2 oz copper pad layout with R_{6JA} = 50°C/W. 6. Pulse width ≤10µS, Duty Cycle ≤1%. 7. Short duration pulse test used to minimize self-heating effect. Notes:













Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOP-8L			
Dim	Min	Max	
Α	-	1.75	
A1	0.08	0.25	
A2	1.40	1.50	
A3	0.20 Typ		
b	0.3	0.5	
D	4.85	4.95	
E	5.90	6.10	
E1	3.80	3.90	
е	1.27 Тур		
h	-	0.35	
L	0.60	0.80	
θ	0°	8°	
All Dimensions in mm			



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)	
Х	0.60	
Y	1.55	
C1	5.4	
C2	1.27	

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